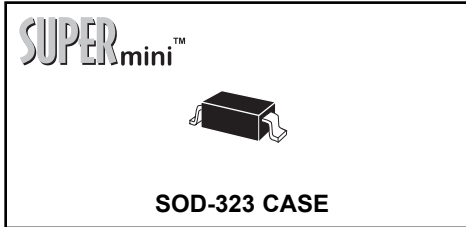


**CMDSH-3**  
**SUPERmini™**  
**SCHOTTKY DIODE**



# Central™

**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMDSH-3 type is a Silicon Schottky diode, manufactured in a SUPERmini™ surface mount package, designed for fast switching applications requiring a low forward voltage drop.

**MARKING CODE: S1**

**MAXIMUM RATINGS** (T<sub>A</sub>=25°C unless otherwise noted)

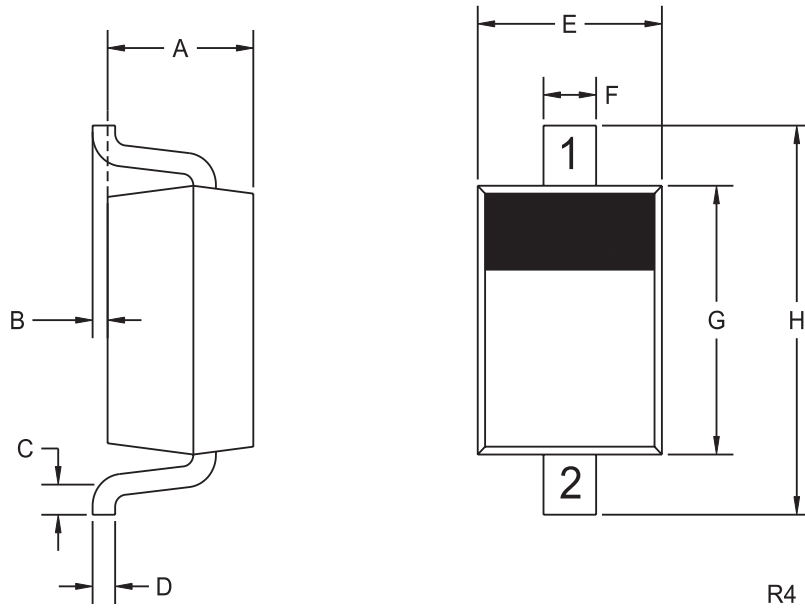
	<b>SYMBOL</b>		<b>UNITS</b>
Peak Repetitive Reverse Voltage	V <sub>R</sub> RM	30	V
Average Forward Current	I <sub>O</sub>	100	mA
Forward Surge Current, tp=10ms	I <sub>F</sub> SM	750	mA
Power Dissipation	P <sub>D</sub>	250	mW
Power Dissipation (T <sub>L</sub> =25°C)	P <sub>D</sub>	833	mW
Operating and Storage			
Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	θ <sub>JA</sub>	500	°C/W
Thermal Resistance	θ <sub>JL</sub>	150	°C/W

**ELECTRICAL CHARACTERISTICS:** (T<sub>A</sub>=25°C)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNITS</b>
BV <sub>R</sub>	I <sub>F</sub> =100μA	30			V
V <sub>F</sub>	I <sub>F</sub> =2.0mA		0.30		V
V <sub>F</sub>	I <sub>F</sub> =15mA		0.36		V
V <sub>F</sub>	I <sub>F</sub> =50mA		0.47	0.55	V
V <sub>F</sub>	I <sub>F</sub> =100mA		0.58	0.80	V
I <sub>R</sub>	V <sub>R</sub> =25V			1.0	μA
C <sub>T</sub>	V <sub>R</sub> =10V, f=1.0 MHz		7.0		pF

R5 (31-October 2002)

**MECHANICAL OUTLINE - SOD-323**



**LEAD CODE:**

- 1) CATHODE
- 2) ANODE

**MARKING CODE: S1**

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.031	0.039	0.80	1.00
B	0.000	0.004	0.00	0.10
C	0.008	-	0.20	-
D	0.004	0.007	0.11	0.19
E	0.045	0.053	1.15	1.35
F	-	0.014	-	0.35
G	0.063	0.071	1.60	1.80
H	0.094	0.102	2.40	2.60

SOD-323 (REV: R4)

R5 (31-October 2002)